imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





NPN SILICON HIGH FREQUENCY TRANSISTOR

FEATURES

- SMALL PACKAGE STYLE: 2 NE688 Die in a 2 mm x 1.25 mm package
- LOW NOISE FIGURE: NF = 1.5 dB TYP at 2 GHz
- HIGH GAIN BANDWIDTH: ft = 9 GHz
- HIGH COLLECTOR CURRENT: 100 mA

DESCRIPTION

NEC's UPA814T is two NPN high frequency silicon epitaxial transistors encapsulated in an ultra small 6 pin SMT package. Each transistor is independently mounted and easily configured for either dual transistor or cascode operation. The high ft, low voltage bias and small size make this device suited for various hand-held wireless applications.

SYMBOLS	PARAMETERS	UNITS	RATINGS			
Vсво	Collector to Base Voltage	V	9			
VCEO	Collector to Emitter Voltage	V	6			
Vebo	Emitter to Base Voltage	V	2			
Ic	Collector Current	mA	100			
Рт	Total Power Dissipation 1 Die 2 Die	mW mW	110 200			
TJ	Junction Temperature	°C	150			
Тѕтс	Storage Temperature	°C	-65 to +150			

ABSOLUTE MAXIMUM RATINGS¹ (TA = 25°C)

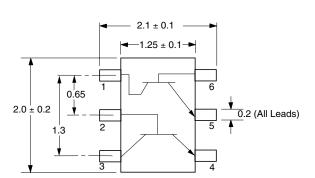
Note: 1.Operation in excess of any one of these parameters may result in permanent damage.

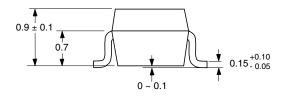
ELECTRICAL CHARACTERISTICS (TA = 25°C)

OUTLINE DIMENSIONS (Units in mm)

PACKAGE OUTLINE S06

UPA814T





PIN OUT

1. Collector Transistor 1

2. Base Transistor 2

3. Collector Transistor 2

4. Emitter Transistor 2 5. Emitter Transistor 1

6. Base Transistor 1

Note:

Pin 3 is identified with a circle on the bottom of the package.

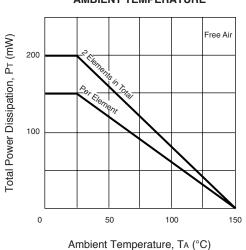
PART NUMBER PACKAGE OUTLINE			UPA814T S06		
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	ТҮР	MAX
Ісво	Collector Cutoff Current at VCB = 5V, IE = 0	μΑ			0.1
Іево	Emitter Cutoff Current at VEB = 1 V, IC = 0	μΑ			0.1
hfe ¹	Forward Current Gain at VCE = 1 V, IC = 3 mA		80	110	160
fτ	Gain Bandwidth at VCE = 3 V, IC = 20 mA, f = 2 GHz	GHz		9.0	
Cre ²	Feedback Capacitance at VCB = 1 V, IE = 0, f = 1 MHz	pF		0.75	0.85
IS21El ²	Insertion Power Gain at VCE = 3 V, IC =20 mA, f = 2 GHz	dB		6.5	
NF	Noise Figure at Vce = 3 V, Ic = 7 mA, f = 2 GHz	dB		1.5	
hfe1/hfe2	hFE Ratio: hFE1 = Smaller Value of Q1, or Q2 hFE2 = Larger Value of Q1 or Q2		0.85		

Notes: 1. Pulsed measurement, pulse width ≤ 350 μ s, duty cycle ≤ 2 %.

2. The emitter terminal should be connected to the ground terminal of the 3 terminal capacitance bridge.

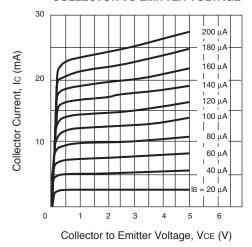
For Tape and Reel version use part number UPA814T-T1, 3K per reel.

TYPICAL PERFORMANCE CURVES (TA = 25°C)

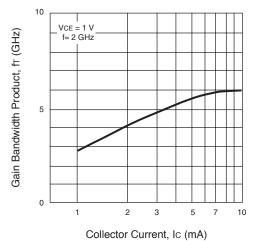


TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE

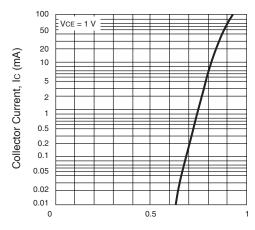
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

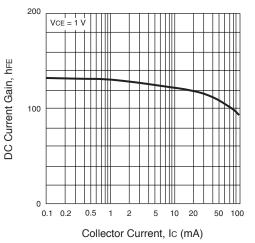


COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

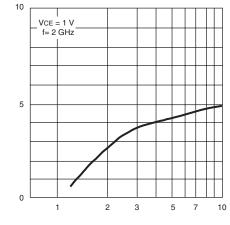


Base to Emitter Voltage, VBE (V)

DC CURRENT GAIN vs. COLLECTOR CURRENT



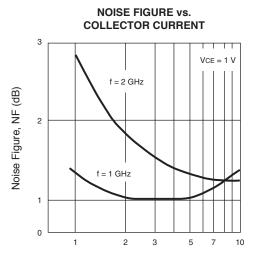
INSERTION POWER GAIN vs. COLLECTOR CURRENT



Insertion Power Gain, IS21el² (dB)

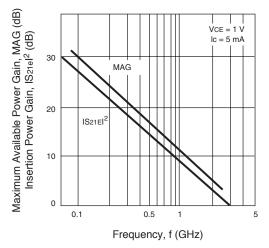
Collector Current, Ic (mA)

TYPICAL PERFORMANCE CURVES (TA = 25°C)

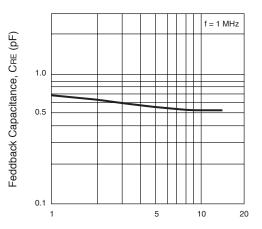


Collector Current, Ic (mA)



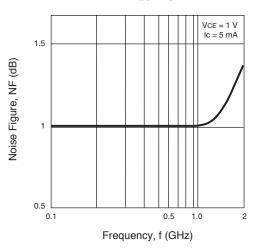


FEEDBACK CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



Collector to Base Voltage, VCB (V)

NOISE FIGURE vs. FREQUENCY



ORDERING INFORMATION

PART NUMBER	QUANTITY	PACKAGING	
UPA814T-T1-A	3000	Tape & Reel	

Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices	
Lead (Pb)	< 1000 PPM	-A Not Detected	-AZ (*)
Mercury	< 1000 PPM	Not Detected	
Cadmium	< 100 PPM	Not Detected	
Hexavalent Chromium	< 1000 PPM	Not Detected	
РВВ	< 1000 PPM	Not Detected	
PBDE	< 1000 PPM	Not Detected	

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

In no event shall CEL's liability arising out of such information exceed the total purchase price of the CEL part(s) at issue sold by CEL to customer on an annual basis.

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